





TPS784-Q1 SBVS387C - FEBRUARY 2020 - REVISED JANUARY 2022

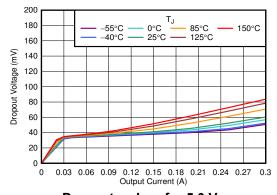
TPS784-Q1 Automotive, 300-mA, High-PSRR Low-Dropout Voltage Regulator With High Accuracy and Enable

1 Features

- AEC-Q100 qualified for automotive applications:
 - Temperature grade 1: –40°C to +125°C, T_A
- Device junction temperature: -40°C to +150°C, T_J
- Input voltage range: 1.65 V to 6.0 V
- Available output voltages:
 - Adjustable option: 1.2 V to 5.5 V
 - Fixed options: 0.65 V to 5.0 V
- Output accuracy: 0.5% typical, 1.7% maximum
- 50-dB PSRR out to 100 kHz
- Low I_O: 25 µA (typical)
- Ultra-low dropout:
 - 115 mV (max) at 300 mA (3.3 V_{OUT})
- Internal 500-µs soft-start time to reduce inrush
- Active output discharge
- Functional Safety-Capable
 - Documentation available to aid functional safety system design
- Packages:
 - 3-mm × 3-mm wettable flank VSON (8)
 - 5-pin SOT-23

2 Applications

- Automotive head units
- Hybrid instrument clusters
- Telematics control units
- DC/DC converters



Dropout vs I_{OUT} for 5.0 V

3 Description

The TPS784-Q1 ultra low-dropout regulator (LDO) is a small, low quiescent current LDO that can source 300 mA with excellent line and load transient performance.

The low output noise and great PSRR performance make the device suitable to power sensitive analog loads. The TPS784-Q1 is a flexible device for post regulation because this device supports an input voltage range from 1.65 V to 6.0 V and offers an adjustable output range of 1.2 V to 5.5 V. The device also features fixed output voltages from 0.65 V to 5.0 V for powering common voltage rails.

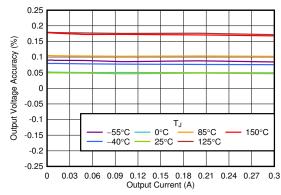
The TPS784-Q1 offers foldback current limit to reduce power dissipation during over current condition. The EN input helps with power sequencing requirements of the system. The internal soft-start provides a controlled start up, reducing the inrush current and allowing for lower input capacitance to be used.

The TPS784-Q1 provides an active pulldown circuit to quickly discharge output loads when disabled.

Device Information⁽¹⁾

PART NUMBER	PACKAGE	BODY SIZE (NOM)
	Wettable flank VSON (8)	3.00 mm × 3.00 mm
	SOT-23 (5)	2.90 mm × 1.60 mm

For all available packages, see the orderable addendum at the end of the data sheet.



Output Accuracy vs I_{OUT} for 5.0 V



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4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

С	changes from May 16, 2021 to January 11, 2022 (from Revision B (April 2021) to Revision C	
(J	January 2022))	Page
•	Changed VSON package from preview to production data	1
•	Added B version DRB package (VSON) to the Pin Configuration and Functions section	3
•	Changed Device Nomenclature table	39
c	hanges from Revision A (November 2020) to Revision B (April 2021)	Page
_		

5 Pin Configuration and Functions

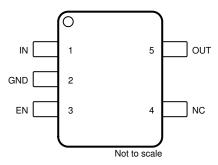


Figure 5-1. DBV Package (Fixed), 5-Pin SOT-23, Top View

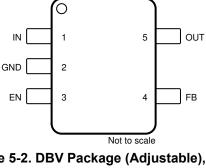


Figure 5-2. DBV Package (Adjustable), 5-Pin SOT-23, Top View

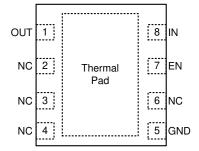


Figure 5-3. DRB Package (Fixed), 8-Pin VSON, Top View

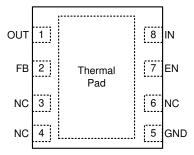


Figure 5-4. DRB Package (Adjustable), 8-Pin VSON, Top View

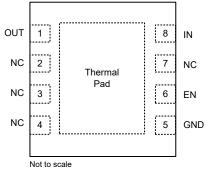


Figure 5-5. DRB Package (Fixed) B Version, 8-Pin VSON, Top View

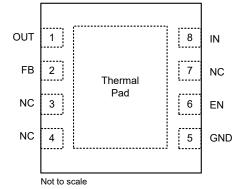


Figure 5-6. DRB Package (Adjustable) B Version, 8-Pin VSON, Top View



Table 5-1. Pin Functions

PIN							Tunct	
NAME	DBV (Adjustable)	DBV (Fixed)	DRB (Adjustable)	DRB (Fixed)	DRB (Adjustable) B Version	DRB (Fixed) B Version	I/O	DESCRIPTION
EN	3	3	7	7	6	6	Input	Enable pin. Driving this pin to logic high enables the device; driving this pin to logic low disables the device. Do not float this pin. If not used, connect EN to IN.
FB	4	_	2	_	2	_	Input	Feedback pin. Input to the control-loop error amplifier. This pin is used to set the output voltage of the device with the use of external resistors. Do not float this pin. For adjustable-voltage version devices only.
GND	2	2	5	5	5	5	_	Ground pin. This pin must be connected to ground on the board.
IN	1	1	8	8	8	8	Input	Input pin. For best transient response and to minimize input impedance, use the recommended value or larger ceramic capacitor from IN to ground; see the <i>Recommended Operating Conditions</i> table. Place the input capacitor as close to the input of the device as possible.
NC	_	4	3, 4, 6	2, 3, 4, 6	3, 4, 7	2, 3, 4, 7	_	No connect pin. This pin is not internally connected. Connect to ground for best thermal performance or leave floating.
OUT	5	5	1	1	1	1	Output	A 0.47-µF or greater effective capacitance is required from OUT to ground for stability. For best transient response, use a 1-µF or larger ceramic capacitor from OUT to ground. Place the output capacitor as close to output of the device as possible; see the Recommended Operating Conditions table.
Thermal Pad	N/A	N/A	Pad	Pad	Pad	Pad	_	The thermal pad is electrically connected to the GND pin. Connect the thermal pad to a large-area GND plane for improved thermal performance.



6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

		MIN	MAX	UNIT
Mallana	Supply, V _{IN}	-0.3	6.5	V
	Enable, V _{EN}	-0.3	6.5	V
Voltage	Output, V _{OUT}	-0.3	$V_{IN} + 0.3^{(2)}$	V
	Feedback, V _{FB}	-0.3	2	V
Current	Output, I _{OUT}	Internally	limited	
Tommoratura	Operating junction, T _J	-40	150	°C
Temperature	Storage, T _{stg}	-65	150	°C

⁽¹⁾ Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

6.2 ESD Ratings

			VALUE	UNIT
V		Human-body model (HBM), per AEC Q100-002 ⁽¹⁾		V
V _(ESD)	Electrostatic discharge	Charged-device model (CDM), per AEC Q100-011	±500	v

(1) AEC Q100-002 indicates that HBM stressing shall be in accordance with the ANSI/ESDA/JEDEC JS-001 specification.

⁽²⁾ The absolute maximum rating is V_{IN} + 0.3 V or 6.5 V, whichever is smaller.



6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

			MIN	NOM	MAX	UNIT
V _{IN}	Input voltage		1.65		6.0	V
V	Output voltage	Adjustable output	1.2		5.5	V
V _{OUT} Output voltage	Fixed output	0.65		5.0	V	
C _{IN}	C _{IN} Input capacitor		0.1	1		μF
C _{OUT}	Output capacitor				200	μF
C _{FF}	Feed-forward capacitor ⁽²⁾			10	100	nF
I _{OUT}	Output current		0		300	mA
C _{OUT,ESR}	Output capacitor ESR		0.001		1	Ω
V _{EN}	Enable voltage				6	V
F _{EN}	Enable toggle frequency				10	kHz
T _J	Junction temperature				150	°C

- (1) The minimum effective capacitance is 0.47 μF.
- (2) Feed-forward capacitor is optional and not required for stability.

6.4 Thermal Information

		TPS	TPS784-Q1			
	THERMAL METRIC ⁽¹⁾	DRB (VSON)	DBV (SOT-23)	UNIT		
		8 PINS	5 PINS			
R _{θJA}	Junction-to-ambient thermal resistance	61.8 ⁽²⁾	170.8 ⁽³⁾	°C/W		
R _{0JC(top)}	Junction-to-case (top) thermal resistance	74.1	93.1	°C/W		
R _{0JB}	Junction-to-board thermal resistance	34.3	10.2	°C/W		
ΨЈТ	Junction-to-top characterization parameter	6.2	17.5	°C/W		
ΨЈВ	Junction-to-board characterization parameter	34.1	40	°C/W		
R _{0JC(bot)}	Junction-to-case (bottom) thermal resistance	18.1	n/a	°C/W		

- (1) For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.
- (2) The 1s0p $R_{\theta JA}$ value (based on JEDEC 51-3) is 226.5 °C/W for the DRB package.
- (3) The 1s0p $R_{\theta JA}$ value (based on JEDEC 51-3) is 277.3 °C/W for the DBV package.

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6.5 Electrical Characteristics

at operating temperature range ($T_J = -40^{\circ}\text{C}$ to +150°C), $V_{IN} = V_{OUT(nom)} + 0.5 \text{ V}$ or 1.65 V (whichever is greater), $I_{OUT} = 1 \text{ mA}$, $V_{EN} = V_{IN}$, and $C_{IN} = C_{OUT} = 1 \text{ \muF}$, unless otherwise noted. All typical values at $T_J = 25^{\circ}\text{C}$.

	PARAMETER	TEST CON	IDITIONS	MIN	TYP	MAX	UNIT
V _{IN}	Input voltage			1.65		6.0	V
		Adjustable output		1.2		5.5	
/ _{OUT}	Output voltage	Fixed output		0.65		5.0	V
		1 mA ≤ I _{OUT} ≤ 300 mA,	T _J = 25°C	-0.5		0.5	
V _{OUT}	Output accuracy ⁽¹⁾	V _{OUT(nom)} + 0.5 V or 1.65 V	-40°C ≤ T _J ≤ 85°C	-1		1	%
		(whichever is greater) ≤ V _{IN} ≤ 6.0 V	-40°C ≤ T _J ≤ 150°C	-1.7		1.7	
V _{OUT}	Line regulation	V _{OUT(nom)} + 0.5 V or 1.65 V (w	/hichever is greater) ≤ V _{IN} ≤		0.3		mV
			–40°C ≤ T _J ≤ 85°C	-5		5	
/ _{OUT}	Load regulation	0.1 mA ≤ I _{OUT} ≤ 300 mA	-40°C ≤ T _J ≤ 150°C	-5		10	mV
	Load transient response settling time ⁽²⁾ (3)	C _{OUT} = 10 μF				10	μs
A			I _{OUT} = 90 mA to 210 mA	-2%			
ΔV _{OUT}	Load transient response overshoot, undershoot (3) (5)	$t_{R} = t_{F} = 1 \text{ µs, } C_{OUT} = 10 \text{ µF}$	I _{OUT} = 210 mA to 90 mA			10%	%V _{OU} -
			I _{OUT} = 0 mA to 300 mA	-10%			
		I _{OUT} = 0 mA	T _J = 25°C	15	25	30	
		V _{OUT(nom)} + 0.5 V or 1.65 V (whichever is greater) ≤ V _{IN} ≤	-40°C ≤ T _J ≤ 85°C			33	
	Cround aurent	6.0 V	-40°C ≤ T _J ≤ 150°C		-	40	
GND	Ground current	I _{OUT} = 500 μA V _{OUT(nom)} + 0.5 V or 1.65 V (whichever is greater) ≤ V _{IN} ≤ 6.0 V	T _J = 25°C		33	43	μA
			-40°C ≤ T _J ≤ 85°C			45	
			-40°C ≤ T _J ≤ 150°C			48	
		V _{EN} ≤ 0.3 V V _{OUT(nom)} + 0.5 V or 1.65 V (whichever is greater) ≤ V _{IN} ≤	T _J = 25°C		0.01	0.05	μΑ
SHDN	Shutdown current		-40°C ≤ T _J ≤ 85°C			0.25	
		6.0 V	-40°C ≤ T _J ≤ 150°C			3	
/ _{FB}	Feedback voltage	Adjustable output only		1.182	1.2	1.218	V
FB	Feedback pin current	Adjustable output only		-0.05	0.01	0.05	μA
CL	Output current limit	$V_{IN} = V_{OUT(nom)} + 1 V,$ $V_{OUT} = 0.9 \times V_{OUT(nom)}$ (4)		320		420	mA
sc	Short-circuit current limit	V _{OUT} = 0 V			162.5		mA
			0.65 V ≤ V _{OUT} < 0.8 V			900	
			0.8 V ≤ V _{OUT} < 1.2 V			775	
			1.2 V ≤ V _{OUT} < 1.5 V			300	
I_{DO}	Dropout voltage	I _{OUT} = 300 mA,	1.5 V ≤ V _{OUT} < 1.8 V			175	
A DO	Diopout voltage	$V_{OUT} = 0.95 \times V_{OUT(nom)}$	1.8 V ≤ V _{OUT} < 2.5 V			140	mV
			2.5 V ≤ V _{OUT} ≤ 5.0 V			115	-
			1.2 V ≤ V _{OUT} < 1.5 V, DRB Package only	,		320	
			f = 1 kHz		60		
PSRR	Power-supply rejection ratio	I _{OUT} = 300 mA , V _{IN} = V _{OUT} + 1 V	f = 100 kHz		45		dB
		VOUTTIV	f = 1 MHz	,	30		
/n	Output noise voltage	BW = 10 Hz to 100 kHz, V _{OUT} = 1.2 V			30		μV _{RM}
		V _{IN} rising		1.32	1.42	1.6	
/ _{UVLO}	UVLO threshold	V _{IN} falling		1.17	1.29	1.42	V
V _{UVLO(HYST)}	UVLO hysteresis	V _{IN} hysteresis			130		mV
STR	Start-up time	From EN low-to-high transition	to V _{OUT} = V _{OUT(nom)} x 95%	280	500	780	μs
• • •	· ·	, , , , , , , , , , , , , , , , , , ,					•
V _{EN(HI)}	EN pin logic high voltage			0.85			V



6.5 Electrical Characteristics (continued)

at operating temperature range (T_J = -40° C to +150°C), V_{IN} = $V_{OUT(nom)}$ + 0.5 V or 1.65 V (whichever is greater), I_{OUT} = 1 mA, V_{EN} = V_{IN} , and C_{IN} = C_{OUT} = 1 μ F, unless otherwise noted. All typical values at T_J = 25°C.

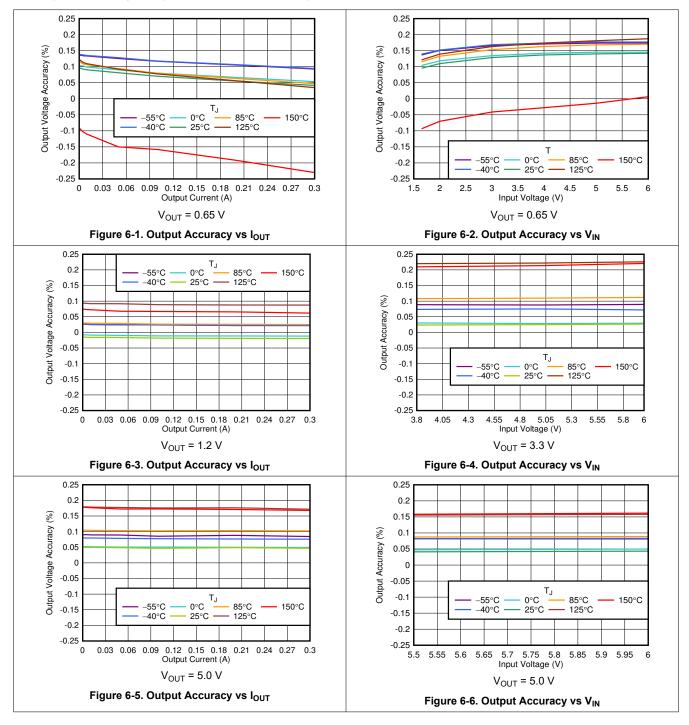
, LIN I	111 - 001 1	·	U			
-	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
I _{EN}	Enable pin current	$V_{IN} = V_{EN} = 6.0 \text{ V}$		10		nA
R _{PULLDOWN}	Pulldown resistance	V _{IN} = 3.3 V		120		Ω
T _{SD(shutdown)}	Thermal shutdown temperature	Shutdown, temperature increasing		170		°C
T _{SD(reset)}	Thermal shutdown reset temperature	Reset, temperature decreasing		155		C

- (1) Resistor tolerance is not included in overall accuracy in the adjustable version.
- (2) The settling time is measured from when I_{OUT} is stepped from 90 mA to 210 mA to when the output voltage recovers to V_{OUT} = V_{OUT(nom)} 5 mV.
- (3) This specification is verified by design.
- (4) The output is being forced to 90% of the nominal V_{OUT} value.
- (5) This specification is in relation to the change from the nominal output voltage (V_{OUT(nom)}).

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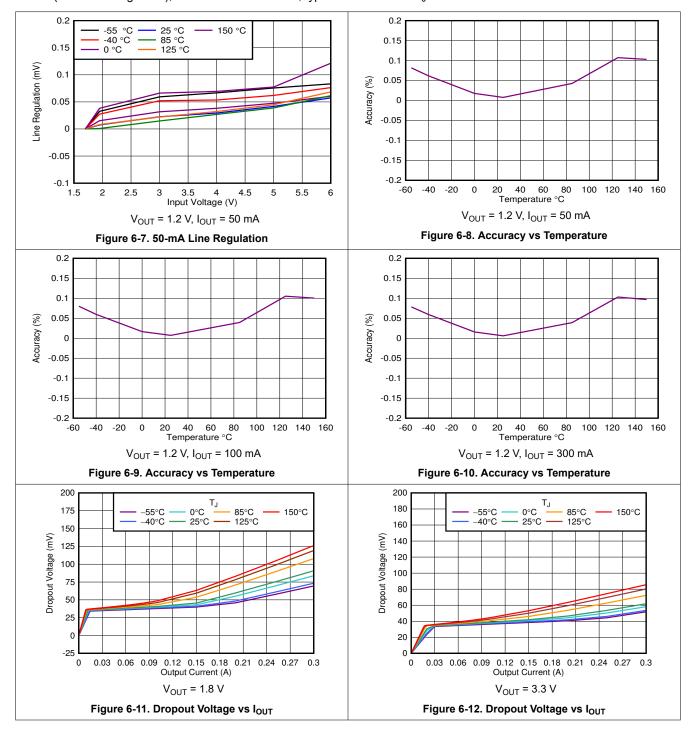
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6.6 Typical Characteristics



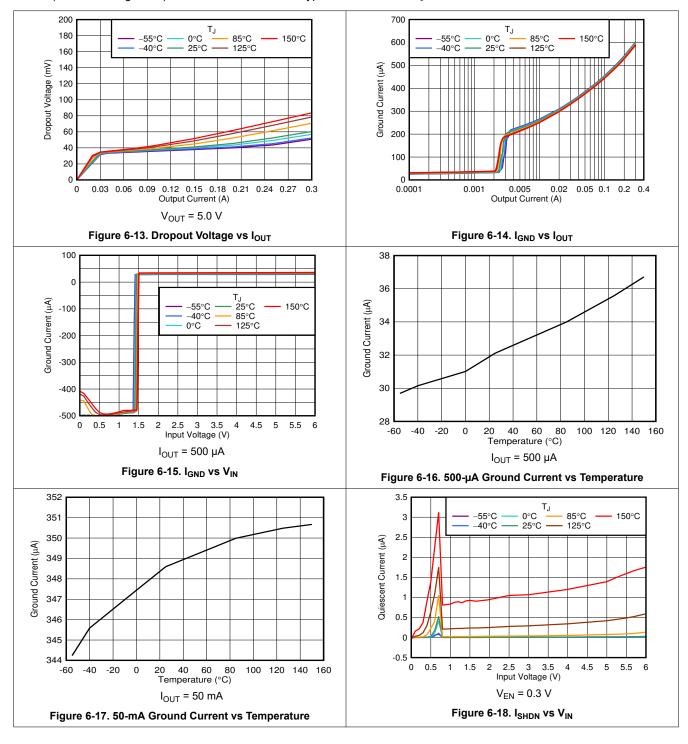


at operating temperature T_J = 25°C, I_{OUT} = 1 mA, V_{EN} = 1.0 V, C_{IN} = 1.0 μ F, C_{OUT} = 1.0 μ F, and V_{IN} = $V_{OUT(NOM)}$ + 0.5 V or 1.65 V (whichever is greater), unless otherwise noted; typical values are at T_J = 25°C



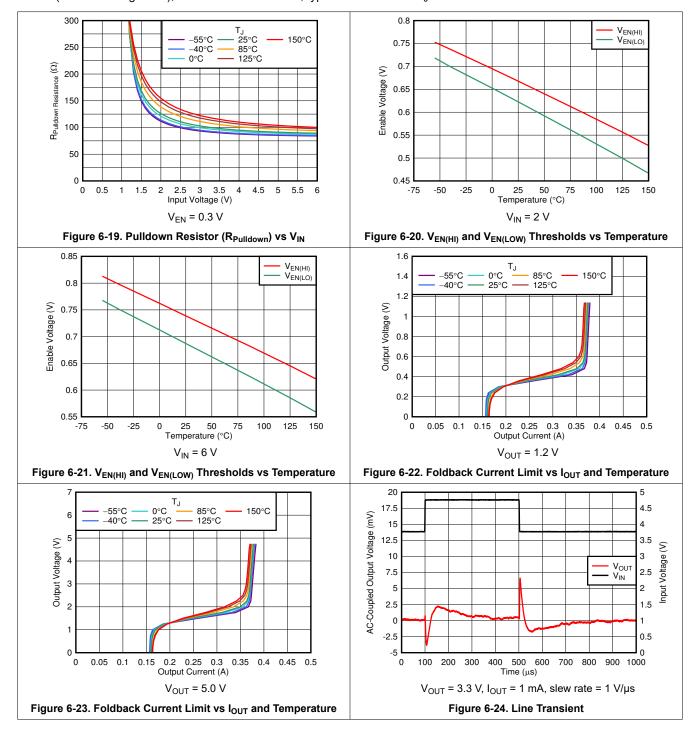
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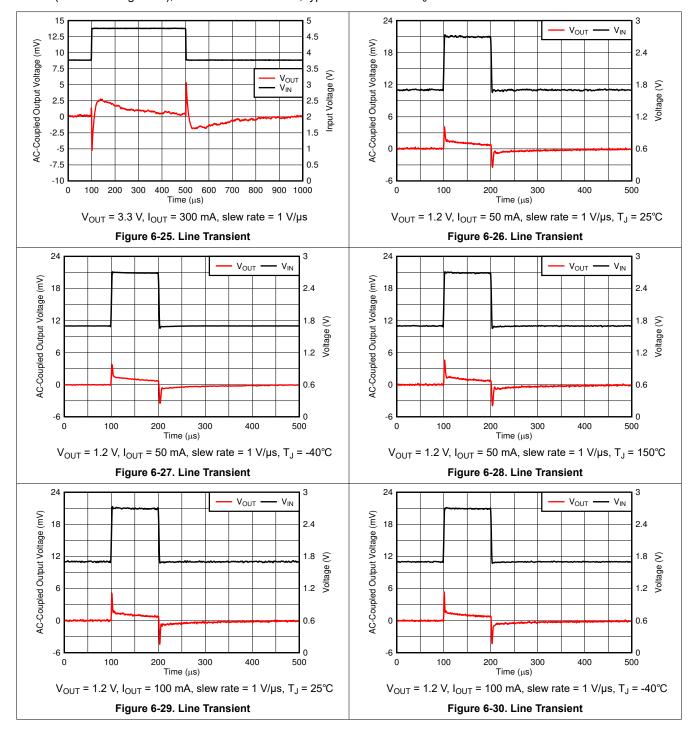
at operating temperature T_J = 25°C, I_{OUT} = 1 mA, V_{EN} = 1.0 V, C_{IN} = 1.0 μ F, C_{OUT} = 1.0 μ F, and V_{IN} = $V_{OUT(NOM)}$ + 0.5 V or 1.65 V (whichever is greater), unless otherwise noted; typical values are at T_J = 25°C



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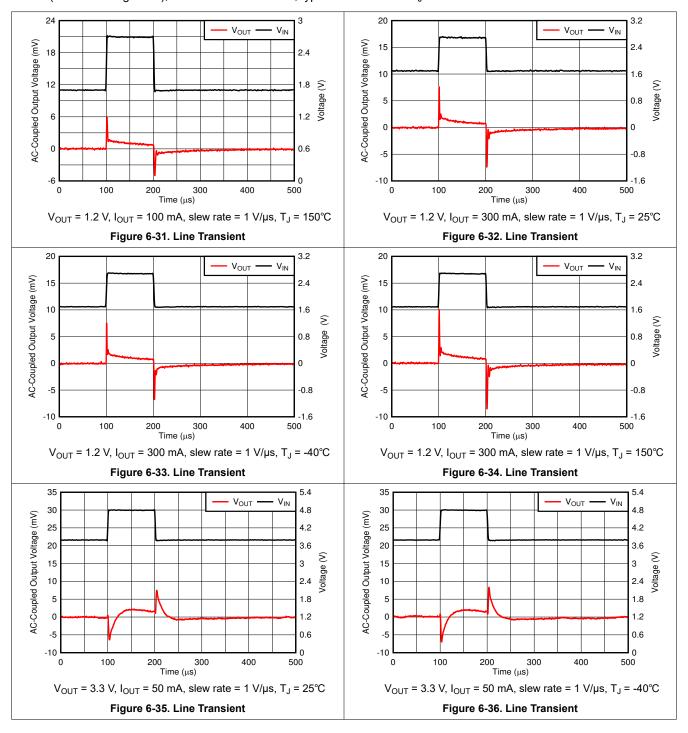


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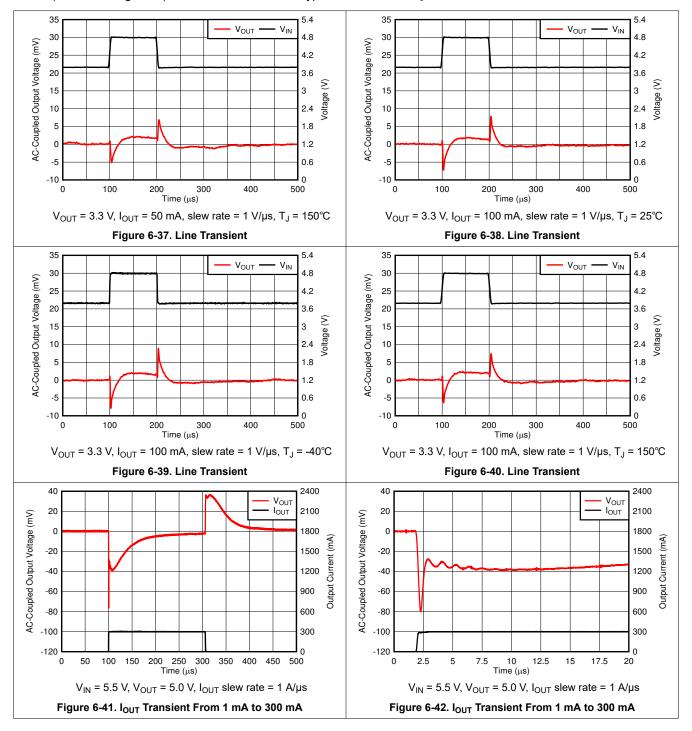
at operating temperature T_J = 25°C, I_{OUT} = 1 mA, V_{EN} = 1.0 V, C_{IN} = 1.0 μ F, C_{OUT} = 1.0 μ F, and V_{IN} = $V_{OUT(NOM)}$ + 0.5 V or 1.65 V (whichever is greater), unless otherwise noted; typical values are at T_J = 25°C



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at operating temperature T_J = 25°C, I_{OUT} = 1 mA, V_{EN} = 1.0 V, C_{IN} = 1.0 μ F, C_{OUT} = 1.0 μ F, and V_{IN} = $V_{OUT(NOM)}$ + 0.5 V or 1.65 V (whichever is greater), unless otherwise noted; typical values are at T_J = 25°C

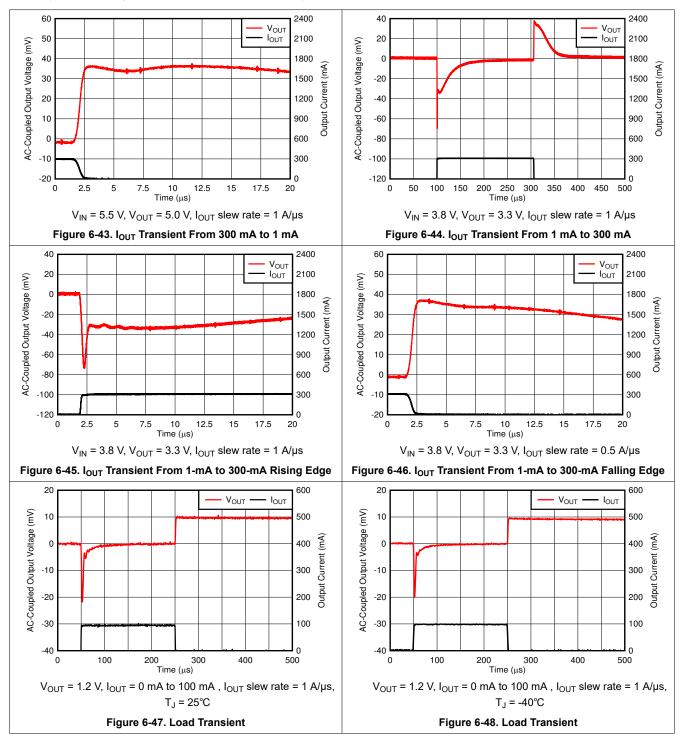


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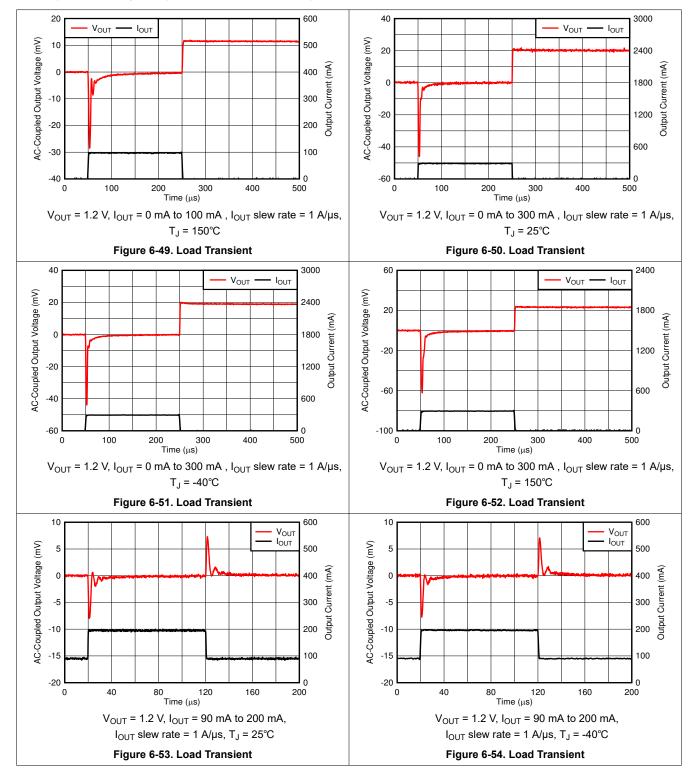


at operating temperature T_J = 25°C, I_{OUT} = 1 mA, V_{EN} = 1.0 V, C_{IN} = 1.0 μ F, C_{OUT} = 1.0 μ F, and V_{IN} = $V_{OUT(NOM)}$ + 0.5 V or 1.65 V (whichever is greater), unless otherwise noted; typical values are at T_J = 25°C

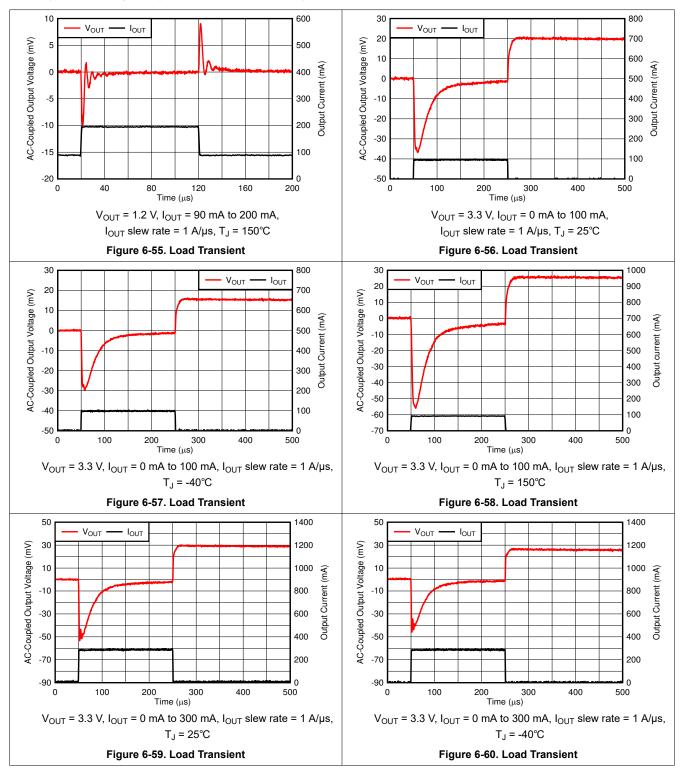


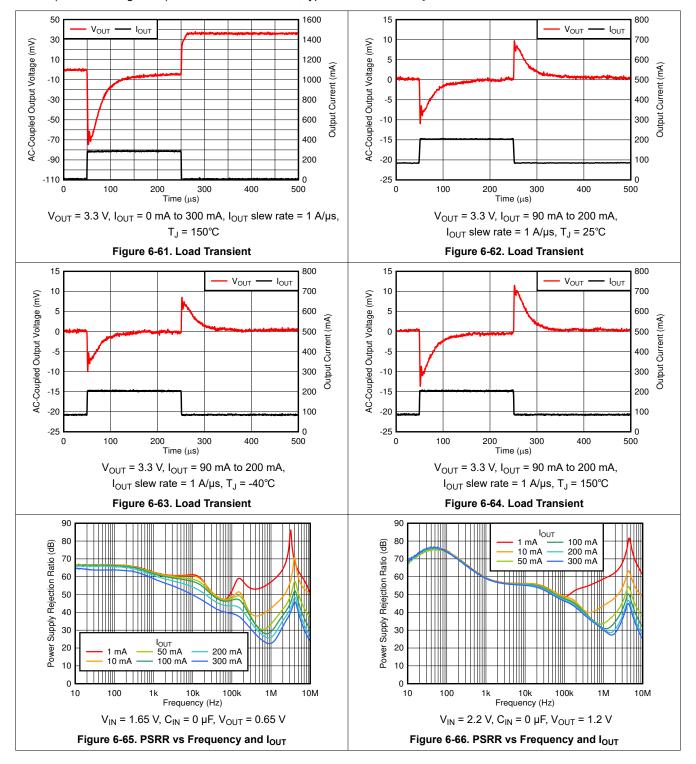
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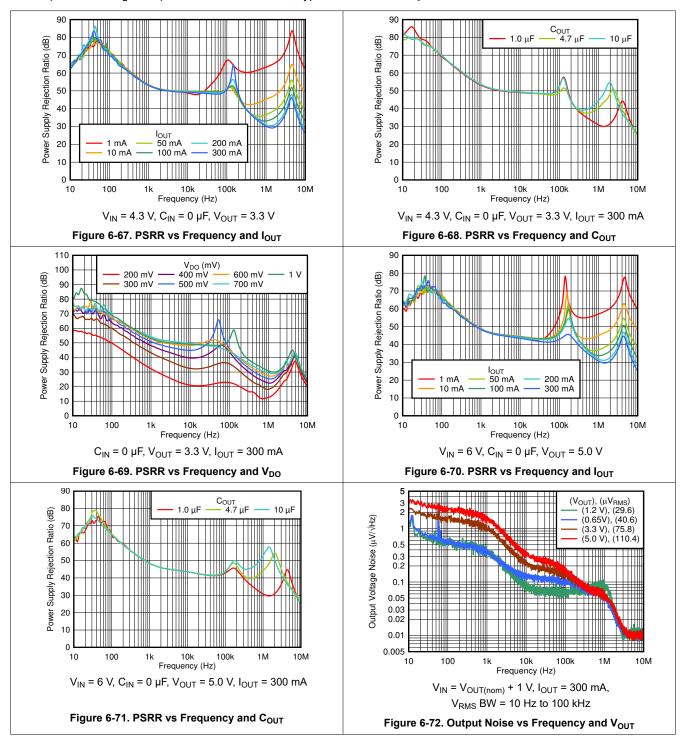


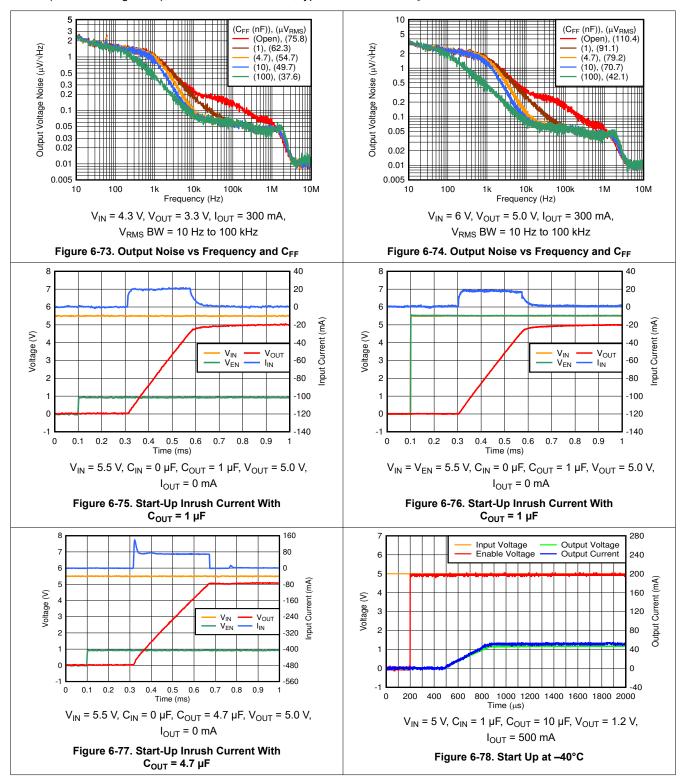






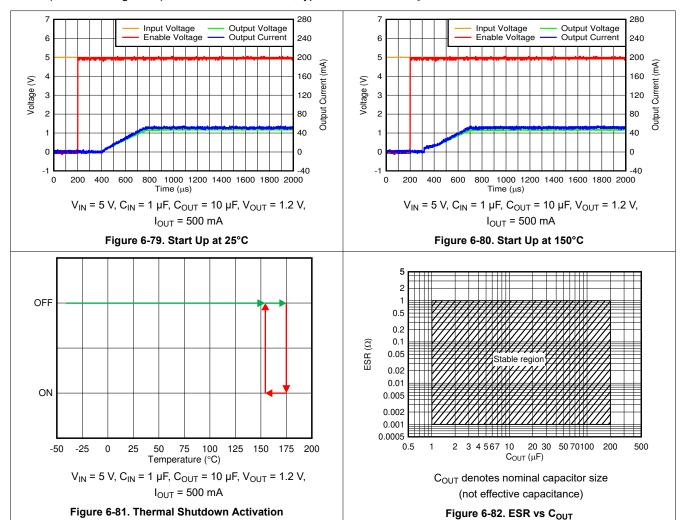








at operating temperature T_J = 25°C, I_{OUT} = 1 mA, V_{EN} = 1.0 V, C_{IN} = 1.0 μ F, C_{OUT} = 1.0 μ F, and V_{IN} = $V_{OUT(NOM)}$ + 0.5 V or 1.65 V (whichever is greater), unless otherwise noted; typical values are at T_J = 25°C



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7 Detailed Description

7.1 Overview

The TPS784-Q1 is an ultra low-dropout, high PSRR, high-accuracy linear voltage regulator that is optimized for excellent transient performance. These characteristics make the device ideal for most automotive applications.

This regulator offers foldback current limit, output enable, active discharge, undervoltage lockout (UVLO), and thermal protection.

7.2 Functional Block Diagrams

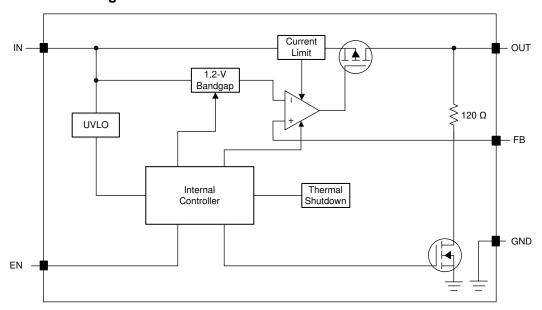


Figure 7-1. Adjustable Version Block Diagram

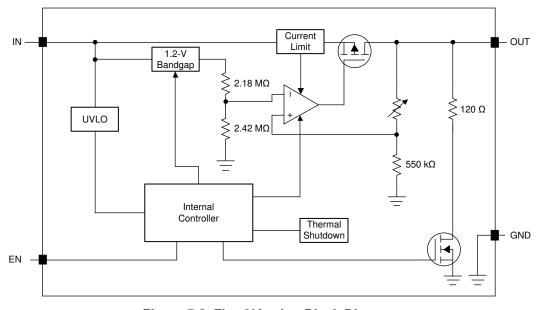


Figure 7-2. Fixed Version Block Diagram

7.3 Feature Description

7.3.1 Foldback Current Limit

The device has an internal current limit circuit that protects the regulator during transient high-load current faults or shorting events. The current limit is a hybrid brickwall-foldback scheme. The current limit transitions from a brickwall scheme to a foldback scheme at the foldback voltage ($V_{FOLDBACK}$). In a high-load current fault with the output voltage above $V_{FOLDBACK}$, the brickwall scheme limits the output current to the current limit (I_{CL}). When the voltage drops below $V_{FOLDBACK}$, a foldback current limit activates that scales back the current as the output voltage approaches GND. When the output is shorted, the device supplies a typical current called the short-circuit current limit (I_{SC}). I_{CL} and I_{SC} are listed in the *Electrical Characteristics* table.

For this device, $V_{FOLDBACK} = 0.4 \times V_{OUT(NOM)}$.

The output voltage is not regulated when the device is in current limit. When a current limit event occurs, the device begins to heat up because of the increase in power dissipation. When the device is in brickwall current limit, the pass transistor dissipates power $[(V_{IN} - V_{OUT}) \times I_{CL}]$. When the device output is shorted and the output is below $V_{FOLDBACK}$, the pass transistor dissipates power $[(V_{IN} - V_{OUT}) \times I_{SC}]$. If thermal shutdown is triggered, the device turns off. After the device cools down, the internal thermal shutdown circuit turns the device back on. If the output current fault condition continues, the device cycles between current limit and thermal shutdown. For more information on current limits, see the *Know Your Limits* application report.

Figure 7-3 shows a diagram of the foldback current limit.

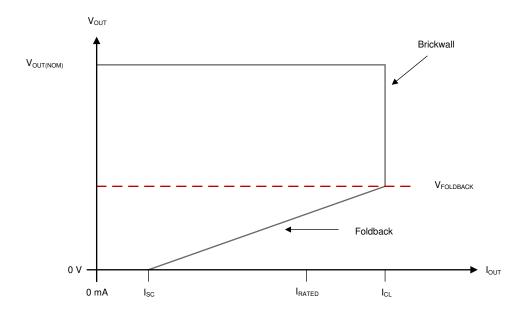


Figure 7-3. Foldback Current Limit

7.3.2 Output Enable

The enable pin (EN) is active high. Enable the device by forcing the voltage of the enable pin to exceed the minimum EN pin high-level input voltage (see the *Electrical Characteristics* table). Turn off the device by forcing the voltage of the enable pin to drop below the maximum EN pin low-level input voltage (see the *Electrical Characteristics* table). If shutdown capability is not required, connect EN to IN.

This device has an internal pulldown circuit that activates when the device is disabled to actively discharge the output voltage.

7.3.3 Active Discharge

The device has an internal pulldown MOSFET that connects an R_{PULLDOWN} resistor to ground when the device is disabled to actively discharge the output voltage. The active discharge circuit is activated by the enable pin.

Do not rely on the active discharge circuit to discharge the output voltage after the input supply has collapsed because reverse current can possibly flow from the output to the input. This reverse current flow can cause damage to the device, especially when a large output capacitor is used. Limit reverse current to no more than 5% of the device rated current for a short period of time.

7.3.4 Undervoltage Lockout (UVLO) Operation

The UVLO circuit ensures that the device stays disabled before its input supply reaches the minimum operational voltage range, and ensures that the device shuts down when the input supply collapses. Figure 7-4 shows the UVLO circuit response to various input voltage events. The diagram can be separated into the following parts:

- Region A: The device does not start until the input reaches the UVLO rising threshold.
- Region B: Normal operation, regulating device.
- Region C: Brownout event above the UVLO falling threshold (UVLO rising threshold UVLO hysteresis). The
 output may fall out of regulation but the device remains enabled.
- · Region D: Normal operation, regulating device.
- Region E: Brownout event below the UVLO falling threshold. The device is disabled in most cases and the
 output falls because of the load and active discharge circuit. The device is reenabled when the UVLO rising
 threshold is reached by the input voltage and a normal start-up follows.
- Region F: Normal operation followed by the input falling to the UVLO falling threshold.
- Region G: The device is disabled when the input voltage falls below the UVLO falling threshold to 0 V. The output falls because of the load and active discharge circuit.

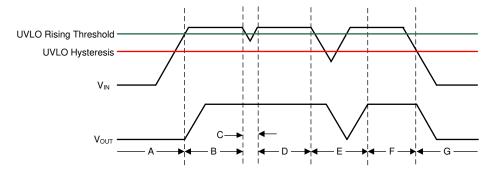


Figure 7-4. Typical UVLO Operation

7.3.5 Dropout Voltage

Dropout voltage (V_{DO}) is defined as the input voltage minus the output voltage $(V_{IN} - V_{OUT})$ at the rated output current (I_{RATED}) , where the pass transistor is fully on. I_{RATED} is the maximum I_{OUT} listed in the *Recommended Operating Conditions* table. The pass transistor is in the ohmic or triode region of operation, and acts as a switch. The dropout voltage indirectly specifies a minimum input voltage greater than the nominal programmed output voltage at which the output voltage is expected to stay in regulation. If the input voltage falls to less than the nominal output regulation, then the output voltage falls as well.

For a CMOS regulator, the dropout voltage is determined by the drain-source on-state resistance ($R_{DS(ON)}$) of the pass transistor. Therefore, if the linear regulator operates at less than the rated current, the dropout voltage for that current scales accordingly. The following equation calculates the $R_{DS(ON)}$ of the device.

$$R_{\rm DS(ON)} = \frac{V_{\rm DO}}{I_{\rm RATED}} \tag{1}$$

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7.3.6 Thermal Shutdown

The device contains a thermal shutdown protection circuit to disable the device when the junction temperature (T_J) of the pass transistor rises to $T_{SD(shutdown)}$ (typical). Thermal shutdown hysteresis assures that the device resets (turns on) when the temperature falls to $T_{SD(reset)}$ (typical).

The thermal time-constant of the semiconductor die is fairly short, thus the device may cycle on and off when thermal shutdown is reached until power dissipation is reduced. Power dissipation during startup can be high from large $V_{\text{IN}} - V_{\text{OUT}}$ voltage drops across the device or from high inrush currents charging large output capacitors. Under some conditions, the thermal shutdown protection disables the device before startup completes.

For reliable operation, limit the junction temperature to the maximum listed in the *Recommended Operating Conditions* table. Operation above this maximum temperature causes the device to exceed its operational specifications. Although the internal protection circuitry of the device is designed to protect against thermal overall conditions, this circuitry is not intended to replace proper heat sinking. Continuously running the device into thermal shutdown or above the maximum recommended junction temperature reduces long-term reliability.

7.4 Device Functional Modes

7.4.1 Device Functional Mode Comparison

The *Device Functional Mode Comparison* table shows the conditions that lead to the different modes of operation. See the *Electrical Characteristics* table for parameter values.

Table 7-1. Device Functional Mode Comparison

OPERATING MODE	PARAMETER						
OPERATING MODE	V _{IN}	V _{EN}	I _{OUT}	T _J			
Normal operation	$V_{IN} > V_{OUT(nom)} + V_{DO}$ and $V_{IN} > V_{IN(min)}$	V _{EN} > V _{EN(HI)}	$I_{OUT} < I_{OUT(max)}$	$T_J < T_{SD(shutdown)}$			
Dropout operation	$V_{IN(min)} < V_{IN} < V_{OUT(nom)} + V_{DO}$	$V_{EN} > V_{EN(HI)}$	$I_{OUT} < I_{OUT(max)}$	$T_J < T_{SD(shutdown)}$			
Disabled (any true condition disables the device)	V _{IN} < V _{UVLO}	V _{EN} < V _{EN(LOW)}	Not applicable	$T_J > T_{SD(shutdown)}$			

7.4.2 Normal Operation

The device regulates to the nominal output voltage when the following conditions are met:

- The input voltage is greater than the nominal output voltage plus the dropout voltage (V_{OUT(nom)} + V_{DO})
- The output current is less than the current limit (I_{OUT} < I_{CL})
- The device junction temperature is less than the thermal shutdown temperature (T_{.I} < T_{SD})
- The enable voltage has previously exceeded the enable rising threshold voltage and has not yet decreased to less than the enable falling threshold

7.4.3 Dropout Operation

If the input voltage is lower than the nominal output voltage plus the specified dropout voltage, but all other conditions are met for normal operation, the device operates in dropout mode. In this mode, the output voltage tracks the input voltage. During this mode, the transient performance of the device becomes significantly degraded because the pass transistor is in the ohmic or triode region, and acts as a switch. Line or load transients in dropout can result in large output-voltage deviations.

When the device is in a steady dropout state (defined as when the device is in dropout, $V_{IN} < V_{OUT(NOM)} + V_{DO}$, directly after being in a normal regulation state, but *not* during start up), the pass transistor is driven into the ohmic or triode region. When the input voltage returns to a value greater than or equal to the nominal output voltage plus the dropout voltage ($V_{OUT(NOM)} + V_{DO}$), the output voltage can overshoot for a short period of time while the device pulls the pass transistor back into the linear region.

7.4.4 Disabled

The output of the device can be shutdown by forcing the voltage of the enable pin to less than the maximum EN pin low-level input voltage (see the *Electrical Characteristics* table). When disabled, the pass transistor is turned off, internal circuits are shutdown, and the output voltage is actively discharged to ground by an internal discharge circuit from the output to ground.

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8 Application and Implementation

Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

8.1 Application Information

8.1.1 Recommended Capacitor Types

The device is designed to be stable using low equivalent series resistance (ESR) ceramic capacitors at the input and output. Multilayer ceramic capacitors have become the industry standard for these types of applications and are recommended, but must be used with good judgment. Ceramic capacitors that employ X7R-, X5R-, and C0G-rated dielectric materials provide relatively good capacitive stability across temperature, whereas the use of Y5V-rated capacitors is discouraged because of large variations in capacitance.

Regardless of the ceramic capacitor type selected, the effective capacitance varies with operating voltage and temperature. As a rule of thumb, expect the effective capacitance to decrease by as much as 50%. The input and output capacitors recommended in the *Recommended Operating Conditions* table account for an effective capacitance of approximately 50% of the nominal value.

8.1.2 Input and Output Capacitor Requirements

The device requires an input capacitor of 1.0 μ F or larger as specified in the *Recommended Operating Conditions* table for stability. A higher value capacitor may be necessary if large, fast rise-time load or line transients are anticipated or if the device is located several inches from the input power source.

The device also requires an output capacitor of 1.0 μ F or larger as specified in the *Recommended Operating Conditions* table for stability. Dynamic performance of the device is improved by using a higher capacitor than the minimum output capacitor.

8.1.3 Adjustable Device Feedback Resistors

The device requires external feedback divider resistors to set the output voltage. Figure 8-1 shows how the output voltage of an adjustable device can be configured from 1.2 V to 5.5 V by using a resistor divider network.

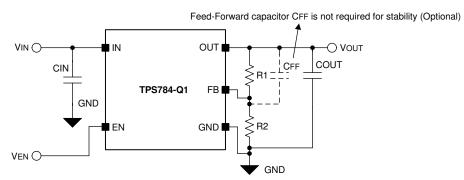


Figure 8-1. Adjustable Operation

Equation 2 calculates the values of the R₁ and R₂ resistors to set the output voltage:

$$V_{OUT} = V_{FB} \times (1 + R_1 / R_2) + I_{FB} \times R_1$$
 (2)

To disregard the effect of the FB pin current error term in Equation 2 and to achieve best accuracy, choose R_2 to be equal to or smaller than 550 k Ω so that the current flowing through R_1 and R_2 is at least 100 times larger than the I_{FB} current listed in the *Electrical Characteristics* table. Lowering the value of R_2 increases the immunity against noise injection. Increasing the value of R_2 reduces the quiescent current for achieving higher efficiency at low load currents. Equation 3 calculates the setting that provides the maximum feedback divider series resistance.

$$(R_1 + R_2) \le V_{OUT} / (I_{FB} \times 100)$$
 (3)

8.1.4 Load Transient Response

The load-step transient response is the output voltage response by the LDO to a step in load current, whereby output voltage regulation is maintained. There are two key transitions during a load transient response: the transition from a light to a heavy load and the transition from a heavy to a light load. The regions shown in Figure 8-2 are broken down as follows. Regions A, E, and H are where the output voltage is in steady-state.

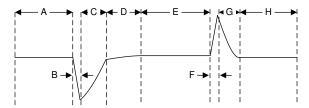


Figure 8-2. Load Transient Waveform

During transitions from a light load to a heavy load, the:

- Initial voltage dip is a result of the depletion of the output capacitor charge and parasitic impedance to the output capacitor (region B)
- Recovery from the dip results from the LDO increasing its sourcing current, and leads to output voltage regulation (region C)
- Initial voltage rise results from the LDO sourcing a large current, and leads to the output capacitor charge to increase (region F)
- Recovery from the rise results from the LDO decreasing its sourcing current in combination with the load discharging the output capacitor (region G)

A larger output capacitance reduces the peaks during a load transient but slows down the response time of the device. A larger DC load also reduces the peaks because the amplitude of the transition is lowered and a higher current discharge path is provided for the output capacitor.

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8.1.5 Exiting Dropout

Some applications have transients that place the LDO into dropout, such as slower ramps on V_{IN} during start-up. As with other LDOs, the output can overshoot on recovery from these conditions. A ramping input supply causes an LDO to overshoot on start-up, as shown in Figure 8-3, when the slew rate and voltage levels are in the correct range. Use an enable signal to avoid this condition.

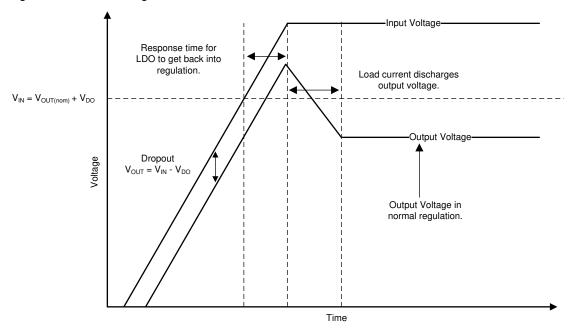


Figure 8-3. Start-Up Into Dropout

Line transients out of dropout can also cause overshoot on the output of the regulator. These overshoots are caused by the error amplifier having to drive the gate capacitance of the pass element and bring the gate back to the correct voltage for proper regulation. Figure 8-4 illustrates what is happening internally with the gate voltage and how overshoot can be caused during operation. When the LDO is placed in dropout, the gate voltage (V_{GS}) is pulled all the way down to ground to give the pass device the lowest on-resistance as possible. However, if a line transient occurs when the device is in dropout, the loop is not in regulation and can cause the output to overshoot until the loop responds and the output current pulls the output voltage back down into regulation. If these transients are not acceptable, then continue to add input capacitance in the system until the transient is slow enough to reduce the overshoot.

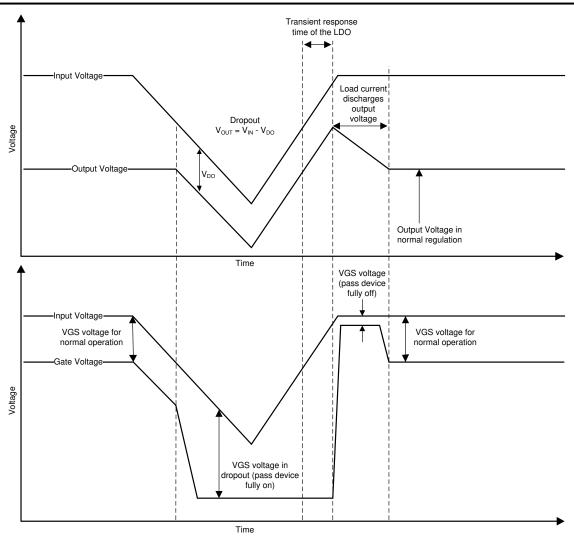


Figure 8-4. Line Transients From Dropout

8.1.6 Dropout Voltage

The device uses a PMOS pass transistor to achieve low dropout. When $(V_{IN}-V_{OUT})$ is less than the dropout voltage (V_{DO}) , the PMOS pass device is in the linear region of operation and the input-to-output resistance is the $R_{DS(ON)}$ of the PMOS pass element. V_{DO} scales approximately with output current because the PMOS device behaves like a resistor in dropout mode. As with any linear regulator, PSRR and transient response degrade as $(V_{IN}-V_{OUT})$ approaches dropout operation.

8.1.7 Reverse Current

As with most LDOs, excessive reverse current can damage this device.

Reverse current flows through the body diode on the pass element instead of the normal conducting channel. At high magnitudes, this current flow degrades the long-term reliability of the device as a result of one of the following conditions:

- · Degradation caused by electromigration
- · Excessive heat dissipation
- Potential for a latch-up condition

Conditions where reverse current can occur are outlined in this section, all of which can exceed the absolute maximum rating of $V_{OUT} > V_{IN} + 0.3 \text{ V}$:

- If the device has a large C_{OUT} and the input supply collapses with little or no load current
- · The output is biased when the input supply is not established
- The output is biased above the input supply

If reverse current flow is expected in the application, external protection must be used to protect the device. Figure 8-5 shows one approach of protecting the device.

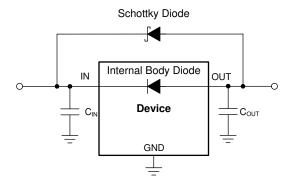


Figure 8-5. Example Circuit for Reverse Current Protection Using a Schottky Diode

8.1.8 Feed-Forward Capacitor (CFF)

For the adjustable-voltage version device, a feed-forward capacitor (C_{FF}) can be connected from the OUT pin to the FB pin. C_{FF} improves transient, noise, and PSRR performance, but is not required for regulator stability. Recommended C_{FF} values are listed in the *Recommended Operating Conditions* table. A higher capacitance C_{FF} can be used; however, the startup time increases. For a detailed description of C_{FF} tradeoffs, see the *Pros and Cons of Using a Feedforward Capacitor with a Low-Dropout Regulator* application report.

8.1.9 Power Dissipation (P_D)

Circuit reliability demands that proper consideration be given to device power dissipation, location of the circuit on the printed circuit board (PCB), and correct sizing of the thermal plane. The PCB area around the regulator must be as free as possible of other heat-generating devices that cause added thermal stresses.

As a first-order approximation, power dissipation in the regulator depends on the input-to-output voltage difference and load conditions. Use Equation 4 to approximate P_D :

$$P_{D} = (V_{IN} - V_{OLIT}) \times I_{OLIT} \tag{4}$$

Power dissipation can be minimized, and thus greater efficiency achieved, by proper selection of the system voltage rails. Proper selection allows the minimum input-to-output voltage differential to be obtained. The low dropout of the TPS784-Q1 allows for maximum efficiency across a wide range of output voltages.

The main heat conduction path for the device is through the thermal pad on the package. As such, the thermal pad must be soldered to a copper pad area under the device. This pad area contains an array of plated vias that conduct heat to any inner plane areas or to a bottom-side copper plane.

The maximum power dissipation determines the maximum allowable junction temperature (T_J) for the device. According to Equation 5, power dissipation and junction temperature are most often related by the junction-to-ambient thermal resistance $(R_{\theta JA})$ of the combined PCB and device package and the temperature of the ambient air (T_A) . Equation 6 rearranges Equation 5 for output current.

$$T_{J} = T_{A} + (R_{\theta JA} \times P_{D}) \tag{5}$$

$$I_{OUT} = (T_J - T_A) / [R_{\theta JA} \times (V_{IN} - V_{OUT})]$$
(6)

Unfortunately, this thermal resistance ($R_{\theta JA}$) is highly dependent on the heat-spreading capability built into the particular PCB design, and therefore varies according to the total copper area, copper weight, and location

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of the planes. The R_{θJA} recorded in the *Recommended Operating Conditions* table is determined by the

JEDEC standard, PCB, and copper-spreading area, and is only used as a relative measure of package thermal performance. For a well-designed thermal layout, $R_{\theta JA}$ is actually the sum of the VSON package junction-to-case (bottom) thermal resistance ($R_{\theta JC(bot)}$) plus the thermal resistance contribution by the PCB copper.

8.1.9.1 Estimating Junction Temperature

The JEDEC standard now recommends the use of psi (Ψ) thermal metrics to estimate the junction temperatures of the LDO when in-circuit on a typical PCB board application. These metrics are not strictly speaking thermal resistances, but rather offer practical and relative means of estimating junction temperatures. These psi metrics are determined to be significantly independent of the copper-spreading area. The key thermal metrics (Ψ_{JT}) and (Ψ_{JB}) are used in accordance with Equation 7 and are given in the *Recommended Operating Conditions* table.

$$\Psi_{JT}: T_J = T_T + \Psi_{JT} \times P_D \text{ and } \Psi_{JB}: T_J = T_B + \Psi_{JB} \times P_D$$
(7)

where:

- P_D is the power dissipated as explained in Equation 4
- T_{T} is the temperature at the center-top of the device package, and
- T_B is the PCB surface temperature measured 1 mm from the device package and centered on the package edge

8.1.9.2 Recommended Area for Continuous Operation

The operational area of an LDO is limited by the dropout voltage, output current, junction temperature, and input voltage. The recommended area for continuous operation for a linear regulator is given in Figure 8-6 and can be separated into the following parts:

- Dropout voltage limits the minimum differential voltage between the input and the output (V_{IN} V_{OUT}) at a
 given output current level. See the *Dropout Voltage* section for more details.
- The rated output currents limits the maximum recommended output current level. Exceeding this rating causes the device to fall out of specification.
- The rated junction temperature limits the maximum junction temperature of the device. Exceeding this rating
 causes the device to fall out of specification and reduces long-term reliability.
 - The shape of the slope is given by Equation 6. The slope is nonlinear because the maximum rated junction temperature of the LDO is controlled by the power dissipation across the LDO; thus when V_{IN} V_{OUT} increases the output current must decrease.
- The rated input voltage range governs both the minimum and maximum of V_{IN} V_{OUT}.

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Figure 8-6 shows the recommended area of operation for this device on a JEDEC-standard high-K board with a R_{0,JA} as given in the *Recommended Operating Conditions* table.

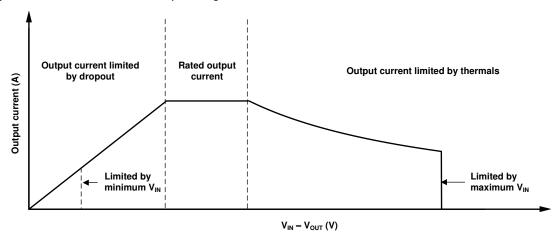


Figure 8-6. Region Description of Continuous Operation Regime

8.1.9.3 Power Dissipation versus Ambient Temperature

Figure 8-7 is based off of a JESD51-7 four-layer high-K board. The allowable power dissipation was estimated using the following equation. As disscussed in the *An empirical analysis of the impact of board layout on LDO thermal performance* application report, thermal dissipation can be improved in the JEDEC high-K layout by adding top layer copper and increasing the number of thermal vias. If a good thermal layout is used, the allowable thermal dissipation can be improved by up to 50%.

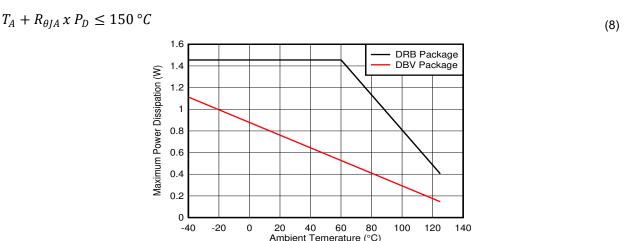


Figure 8-7. Allowable Power Dissipation

8.2 Typical Application

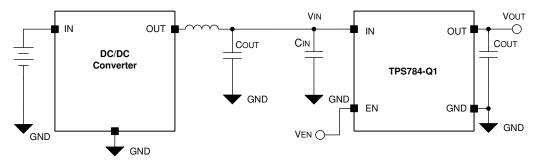


Figure 8-8. Operation From a DC/DC Converter

8.2.1 Design Requirements

Table 8-1 summarizes the design requirement for this application.

Table 8-1. Design Parameters

PARAMETER	DESIGN REQUIREMENT	
Input voltage	3.8 V	
Output voltage	3.3 V, ±1.5%	
Output load	100 mA	
Output capacitor	10 μF	
Maximum ambient temperature	85°C	

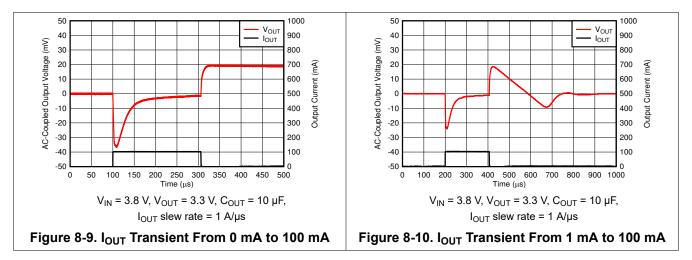
8.2.2 Detailed Design Procedure

For this design example, the 3.3-V, fixed-version device is selected. The device is powered of a DC/DC converter connected to a battery. A 500-mV headroom between V_{IN} and V_{OUT} is used to keep the device within the dropout voltage specification and to ensure the device stays in regulation under all load and temperature conditions for this design.



8.2.3 Application Curves

A 10- μ F capacitor is used to reduce overshoot and undershoot of output voltage during load transients with ramps rates greater than 0.5 A/ μ s. Figure 8-9 and Figure 8-10 show captures of load transient behavior for this application.



9 Power Supply Recommendations

This device is designed to operate from an input supply voltage range of 1.65 V to 6.0 V. The input supply must be well regulated and free of spurious noise. To ensure that the output voltage is well regulated and dynamic performance is optimum, the input supply must be at least $V_{OUT(nom)} + 0.5$ V. TI requires using a 1- μ F or greater input capacitor to reduce the impedance of the input supply, especially during transients.

10 Layout

10.1 Layout Guidelines

- Place input and output capacitors as close to the device as possible.
- Use copper planes for device connections in order to optimize thermal performance.
- Place thermal vias around the device to distribute the heat.
- Only place tented thermal vias directly beneath the thermal pad of the DRB package. An untented via can
 wick solder or solder paste away from the thermal pad joint during the soldering process, leading to a
 compromised solder joint on the thermal pad.

10.1.1 Additional Layout Considerations

The high impedance of the FB pin makes the regulator sensitive to parasitic capacitances that may couple undesirable signals from nearby components (especially from logic and digital devices, such as microcontrollers and microprocessors); these capacitively-coupled signals may produce undesirable output voltage transients. In these cases, TI recommends using a fixed-voltage version of the device, or isolating the FB node by placing a copper ground plane on the layer directly underneath the LDO circuitry and FB pin to minimize any undesirable signal coupling.

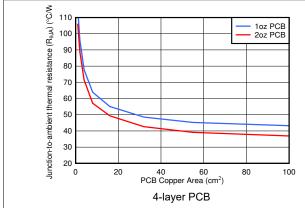


Figure 10-1. Junction-to-Ambient Thermal Resistance ($R_{\theta,JA}$) vs PCB Copper Area

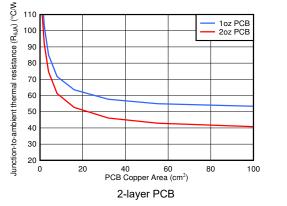


Figure 10-2. Junction-to-Ambient Thermal Resistance ($R_{\theta,JA}$) vs PCB Copper Area

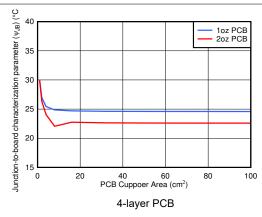


Figure 10-3. Junction-to-Board Characterization Parameter (ψ_{JB}) vs PCB Copper Area

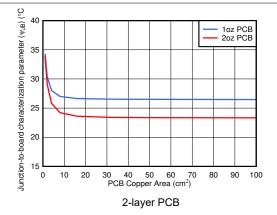
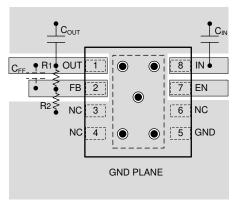


Figure 10-4. Junction-to-Board Characterization Parameter (ψ_{JB}) vs PCB Copper Area



10.2 Layout Examples



Represents a thermal via

C_{OUT} **♦** OUT ΕN NC NC 3 NC GND NC 4 **GND PLANE**

Represents a thermal via

Figure 10-5. Layout Example for the DRB Package **Adjustable Version**

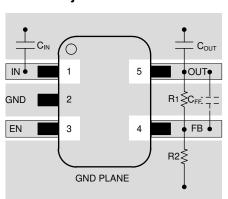


Figure 10-6. Layout Example for the DRB Package **Fixed Version**

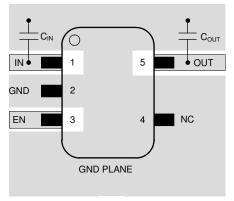


Figure 10-7. Layout Example for the DBV Package Figure 10-8. Layout Example for the DBV Package Adjustable Version

Fixed Version

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11 Device and Documentation Support

11.1 Device Support

11.1.1 Device Nomenclature

Table 11-1. Device Nomenclature

PRODUCT ⁽¹⁾ (2)	V _{OUT}
TPS784xx(x)ZQ(W)yyyRQ1	 xx(x) is the nominal output voltage. For output voltages with a resolution of 100 mV, two digits are used in the ordering number; otherwise, three digits are used (for example, 285 = 2.85 V). Z indicates the pinout of the device. If no letter is present, the EN pin is pin 7, if the B version is used, EN is now pin 6. yyy is the package designator. W is used to denote a wettable flank package.

- (1) For the most current package and ordering information see the *Package Option Addendum* at the end of this document, or visit the device product folder on www.ti.com.
- (2) Output voltages from 0.65 V to 5.5 V in 50-mV increments are available. Contact the factory for details and availability.

11.2 Documentation Support

11.2.1 Related Documentation

For related documentation see the following:

- Texas Instruments, *Universal Low-Dropout (LDO) Linear Voltage Regulator MultiPkgLDOEVM-823 Evaluation Module* user's guide
- Texas Instruments, Pros and Cons of Using a Feedforward Capacitor with a Low-Dropout Regulator application report
- Texas Instruments, An empirical analysis of the impact of board layout on LDO thermal performance application report

11.3 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Subscribe to updates* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

11.4 Support Resources

TI E2E[™] support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

11.5 Trademarks

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11.6 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

11.7 Glossary

TI Glossary

This glossary lists and explains terms, acronyms, and definitions.



12 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

www.ti.com 16-Oct-2025

PACKAGING INFORMATION

Orderable part number	Status	Material type	Package Pins	Package qty Carrier	RoHS	Lead finish/ Ball material	MSL rating/ Peak reflow	Op temp (°C)	Part marking (6)
TPS78401BQWDRBRQ1	Active	Production	SON (DRB) 8	3000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 150	8401BQ
TPS78401BQWDRBRQ1.A	Active	Production	SON (DRB) 8	3000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 150	8401BQ
TPS78401QDBVRQ1	Active	Production	SOT-23 (DBV) 5	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 150	23JF
TPS78401QDBVRQ1.A	Active	Production	SOT-23 (DBV) 5	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 150	23JF
TPS78401QDBVRQ1.B	Active	Production	SOT-23 (DBV) 5	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 150	23JF
TPS78401QWDRBRQ1	Active	Production	SON (DRB) 8	3000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 150	8401WQ
TPS78401QWDRBRQ1.A	Active	Production	SON (DRB) 8	3000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 150	8401WQ
TPS784075QWDRBRQ1	Active	Production	SON (DRB) 8	3000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 150	84075W
TPS784075QWDRBRQ1.A	Active	Production	SON (DRB) 8	3000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 150	84075W
TPS784085BQWDRBRQ1	Active	Production	SON (DRB) 8	3000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 150	4085BQ
TPS784085BQWDRBRQ1.A	Active	Production	SON (DRB) 8	3000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 150	4085BQ
TPS78408BQWDRBRQ1	Active	Production	SON (DRB) 8	3000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 150	8408BQ
TPS78408BQWDRBRQ1.A	Active	Production	SON (DRB) 8	3000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 150	8408BQ
TPS78408QDBVRQ1	Active	Production	SOT-23 (DBV) 5	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 150	2BGF
TPS78408QDBVRQ1.A	Active	Production	SOT-23 (DBV) 5	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 150	2BGF
TPS78408QDBVRQ1.B	Active	Production	SOT-23 (DBV) 5	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 150	2BGF
TPS784105QWDRBRQ1	Active	Production	SON (DRB) 8	3000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 150	84105W
TPS784105QWDRBRQ1.A	Active	Production	SON (DRB) 8	3000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 150	84105W
TPS78410QWDRBRQ1	Active	Production	SON (DRB) 8	3000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 150	8410WQ
TPS78410QWDRBRQ1.A	Active	Production	SON (DRB) 8	3000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 150	8410WQ
TPS78411QWDRBRQ1	Active	Production	SON (DRB) 8	3000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 150	8411WQ
TPS78411QWDRBRQ1.A	Active	Production	SON (DRB) 8	3000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 150	8411WQ
TPS78412BQWDRBRQ1	Active	Production	SON (DRB) 8	3000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 150	8412BQ
TPS78412BQWDRBRQ1.A	Active	Production	SON (DRB) 8	3000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 150	8412BQ
TPS78412QDBVRQ1	Active	Production	SOT-23 (DBV) 5	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 150	23KF
TPS78412QDBVRQ1.A	Active	Production	SOT-23 (DBV) 5	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 150	23KF
TPS78412QDBVRQ1.B	Active	Production	SOT-23 (DBV) 5	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 150	23KF
TPS78412QWDRBRQ1	Active	Production	SON (DRB) 8	3000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 150	8412WQ
TPS78412QWDRBRQ1.A	Active	Production	SON (DRB) 8	3000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 150	8412WQ





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Orderable part number	Status	Material type	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material	MSL rating/ Peak reflow	Op temp (°C)	Part marking (6)
TPS78415QDBVRQ1	Active	Production	SOT-23 (DBV) 5	3000 LARGE T&R	Yes	NIPDAU SN	Level-1-260C-UNLIM	-40 to 150	23LF
TPS78415QDBVRQ1.A	Active	Production	SOT-23 (DBV) 5	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 150	23LF
TPS78415QDBVRQ1.B	Active	Production	SOT-23 (DBV) 5	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 150	23LF
TPS78415QWDRBRQ1	Active	Production	SON (DRB) 8	3000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 150	8415WQ
TPS78415QWDRBRQ1.A	Active	Production	SON (DRB) 8	3000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 150	8415WQ
TPS78417QDBVRQ1	Active	Production	SOT-23 (DBV) 5	3000 LARGE T&R	Yes	NIPDAU SN	Level-1-260C-UNLIM	-40 to 150	2BHF
TPS78417QDBVRQ1.A	Active	Production	SOT-23 (DBV) 5	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 150	2BHF
TPS78417QDBVRQ1.B	Active	Production	SOT-23 (DBV) 5	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 150	2BHF
TPS78418BQWDRBRQ1	Active	Production	SON (DRB) 8	3000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 150	8418BQ
TPS78418BQWDRBRQ1.A	Active	Production	SON (DRB) 8	3000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 150	8418BQ
TPS78418QDBVRQ1	Active	Production	SOT-23 (DBV) 5	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 150	23MF
TPS78418QDBVRQ1.A	Active	Production	SOT-23 (DBV) 5	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 150	23MF
TPS78418QDBVRQ1.B	Active	Production	SOT-23 (DBV) 5	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 150	23MF
TPS78418QWDRBRQ1	Active	Production	SON (DRB) 8	3000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 150	8418WQ
TPS78418QWDRBRQ1.A	Active	Production	SON (DRB) 8	3000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 150	8418WQ
TPS78425BQWDRBRQ1	Active	Production	SON (DRB) 8	3000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 150	8425BQ
TPS78425BQWDRBRQ1.A	Active	Production	SON (DRB) 8	3000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 150	8425BQ
TPS78425QDBVRQ1	Active	Production	SOT-23 (DBV) 5	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 150	23NF
TPS78425QDBVRQ1.A	Active	Production	SOT-23 (DBV) 5	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 150	23NF
TPS78425QDBVRQ1.B	Active	Production	SOT-23 (DBV) 5	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 150	23NF
TPS78425QWDRBRQ1	Active	Production	SON (DRB) 8	3000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 150	8425WQ
TPS78425QWDRBRQ1.A	Active	Production	SON (DRB) 8	3000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 150	8425WQ
TPS78428QDBVRQ1	Active	Production	SOT-23 (DBV) 5	3000 LARGE T&R	Yes	NIPDAU SN	Level-1-260C-UNLIM	-40 to 150	230F
TPS78428QDBVRQ1.A	Active	Production	SOT-23 (DBV) 5	3000 LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 150	230F
TPS78428QDBVRQ1.B	Active	Production	SOT-23 (DBV) 5	3000 LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 150	230F
TPS78429QDBVRQ1	Active	Production	SOT-23 (DBV) 5	3000 LARGE T&R	Yes	NIPDAU SN	Level-1-260C-UNLIM	-40 to 150	23PF
TPS78429QDBVRQ1.A	Active	Production	SOT-23 (DBV) 5	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 150	23PF
TPS78429QDBVRQ1.B	Active	Production	SOT-23 (DBV) 5	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 150	23PF
TPS78430QDBVRQ1	Active	Production	SOT-23 (DBV) 5	3000 LARGE T&R	Yes	NIPDAU SN	Level-1-260C-UNLIM	-40 to 150	23QF
TPS78430QDBVRQ1.A	Active	Production	SOT-23 (DBV) 5	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 150	23QF
TPS78430QDBVRQ1.B	Active	Production	SOT-23 (DBV) 5	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 150	23QF



-40 to 150

-40 to 150

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8450WQ

8450WQ



TPS78450QWDRBRQ1

TPS78450QWDRBRQ1.A

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Orderable part number	Status	Material type	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material	MSL rating/ Peak reflow	Op temp (°C)	Part marking
	(1)	(2)			(3)	(4)	(5)		(6)
TPS78430QWDRBRQ1	Active	Production	SON (DRB) 8	3000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 150	8430WQ
TPS78430QWDRBRQ1.A	Active	Production	SON (DRB) 8	3000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 150	8430WQ
TPS78433BQWDRBRQ1	Active	Production	SON (DRB) 8	3000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 150	8433BQ
TPS78433BQWDRBRQ1.A	Active	Production	SON (DRB) 8	3000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 150	8433BQ
TPS78433QDBVRQ1	Active	Production	SOT-23 (DBV) 5	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 150	23RF
TPS78433QDBVRQ1.A	Active	Production	SOT-23 (DBV) 5	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 150	23RF
TPS78433QDBVRQ1.B	Active	Production	SOT-23 (DBV) 5	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 150	23RF
TPS78433QWDRBRQ1	Active	Production	SON (DRB) 8	3000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 150	8433WQ
TPS78433QWDRBRQ1.A	Active	Production	SON (DRB) 8	3000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 150	8433WQ
TPS78450QDBVRQ1	Active	Production	SOT-23 (DBV) 5	3000 LARGE T&R	Yes	NIPDAU SN	Level-1-260C-UNLIM	-40 to 150	2BIF
TPS78450QDBVRQ1.A	Active	Production	SOT-23 (DBV) 5	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 150	2BIF
TPS78450QDBVRQ1.B	Active	Production	SOT-23 (DBV) 5	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 150	2BIF
			·		·	·			

Active

Active

Yes

Yes

NIPDAU

NIPDAU

Level-2-260C-1 YEAR

Level-2-260C-1 YEAR

3000 | LARGE T&R

3000 | LARGE T&R

Production

Production

SON (DRB) | 8

SON (DRB) | 8

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

⁽¹⁾ Status: For more details on status, see our product life cycle.

⁽²⁾ Material type: When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ RoHS values: Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

⁽⁴⁾ Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

⁽⁵⁾ MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

⁽⁶⁾ Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

PACKAGE OPTION ADDENDUM

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OTHER QUALIFIED VERSIONS OF TPS784-Q1:

Catalog: TPS784

NOTE: Qualified Version Definitions:

Catalog - TI's standard catalog product



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TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TPS78401BQWDRBRQ1	SON	DRB	8	3000	330.0	12.4	3.3	3.3	1.1	8.0	12.0	Q3
TPS78401QDBVRQ1	SOT-23	DBV	5	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TPS78401QWDRBRQ1	SON	DRB	8	3000	330.0	12.4	3.3	3.3	1.1	8.0	12.0	Q3
TPS784075QWDRBRQ1	SON	DRB	8	3000	330.0	12.4	3.3	3.3	1.1	8.0	12.0	Q3
TPS784085BQWDRBRQ1	SON	DRB	8	3000	330.0	12.4	3.3	3.3	1.1	8.0	12.0	Q3
TPS78408BQWDRBRQ1	SON	DRB	8	3000	330.0	12.4	3.3	3.3	1.1	8.0	12.0	Q3
TPS78408QDBVRQ1	SOT-23	DBV	5	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TPS78408QDBVRQ1	SOT-23	DBV	5	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TPS784105QWDRBRQ1	SON	DRB	8	3000	330.0	12.4	3.3	3.3	1.1	8.0	12.0	Q3
TPS78410QWDRBRQ1	SON	DRB	8	3000	330.0	12.4	3.3	3.3	1.1	8.0	12.0	Q3
TPS78411QWDRBRQ1	SON	DRB	8	3000	330.0	12.4	3.3	3.3	1.1	8.0	12.0	Q3
TPS78412BQWDRBRQ1	SON	DRB	8	3000	330.0	12.4	3.3	3.3	1.1	8.0	12.0	Q3
TPS78412QDBVRQ1	SOT-23	DBV	5	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TPS78412QDBVRQ1	SOT-23	DBV	5	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TPS78412QWDRBRQ1	SON	DRB	8	3000	330.0	12.4	3.3	3.3	1.1	8.0	12.0	Q3
TPS78415QDBVRQ1	SOT-23	DBV	5	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3



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Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TPS78415QWDRBRQ1	SON	DRB	8	3000	330.0	12.4	3.3	3.3	1.1	8.0	12.0	Q3
TPS78417QDBVRQ1	SOT-23	DBV	5	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TPS78417QDBVRQ1	SOT-23	DBV	5	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TPS78418BQWDRBRQ1	SON	DRB	8	3000	330.0	12.4	3.3	3.3	1.1	8.0	12.0	Q3
TPS78418QDBVRQ1	SOT-23	DBV	5	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TPS78418QDBVRQ1	SOT-23	DBV	5	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TPS78418QWDRBRQ1	SON	DRB	8	3000	330.0	12.4	3.3	3.3	1.1	8.0	12.0	Q3
TPS78425BQWDRBRQ1	SON	DRB	8	3000	330.0	12.4	3.3	3.3	1.1	8.0	12.0	Q3
TPS78425QDBVRQ1	SOT-23	DBV	5	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TPS78425QDBVRQ1	SOT-23	DBV	5	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TPS78425QWDRBRQ1	SON	DRB	8	3000	330.0	12.4	3.3	3.3	1.1	8.0	12.0	Q3
TPS78428QDBVRQ1	SOT-23	DBV	5	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TPS78429QDBVRQ1	SOT-23	DBV	5	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TPS78430QDBVRQ1	SOT-23	DBV	5	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TPS78430QWDRBRQ1	SON	DRB	8	3000	330.0	12.4	3.3	3.3	1.1	8.0	12.0	Q3
TPS78433BQWDRBRQ1	SON	DRB	8	3000	330.0	12.4	3.3	3.3	1.1	8.0	12.0	Q3
TPS78433QDBVRQ1	SOT-23	DBV	5	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TPS78433QDBVRQ1	SOT-23	DBV	5	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TPS78433QWDRBRQ1	SON	DRB	8	3000	330.0	12.4	3.3	3.3	1.1	8.0	12.0	Q3
TPS78450QDBVRQ1	SOT-23	DBV	5	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TPS78450QWDRBRQ1	SON	DRB	8	3000	330.0	12.4	3.3	3.3	1.1	8.0	12.0	Q3



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*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TPS78401BQWDRBRQ1	SON	DRB	8	3000	367.0	367.0	35.0
TPS78401QDBVRQ1	SOT-23	DBV	5	3000	210.0	185.0	35.0
TPS78401QWDRBRQ1	SON	DRB	8	3000	367.0	367.0	35.0
TPS784075QWDRBRQ1	SON	DRB	8	3000	367.0	367.0	35.0
TPS784085BQWDRBRQ1	SON	DRB	8	3000	367.0	367.0	35.0
TPS78408BQWDRBRQ1	SON	DRB	8	3000	367.0	367.0	35.0
TPS78408QDBVRQ1	SOT-23	DBV	5	3000	210.0	185.0	35.0
TPS78408QDBVRQ1	SOT-23	DBV	5	3000	210.0	185.0	35.0
TPS784105QWDRBRQ1	SON	DRB	8	3000	367.0	367.0	35.0
TPS78410QWDRBRQ1	SON	DRB	8	3000	367.0	367.0	35.0
TPS78411QWDRBRQ1	SON	DRB	8	3000	367.0	367.0	35.0
TPS78412BQWDRBRQ1	SON	DRB	8	3000	367.0	367.0	35.0
TPS78412QDBVRQ1	SOT-23	DBV	5	3000	210.0	185.0	35.0
TPS78412QDBVRQ1	SOT-23	DBV	5	3000	210.0	185.0	35.0
TPS78412QWDRBRQ1	SON	DRB	8	3000	367.0	367.0	35.0
TPS78415QDBVRQ1	SOT-23	DBV	5	3000	210.0	185.0	35.0
TPS78415QWDRBRQ1	SON	DRB	8	3000	367.0	367.0	35.0
TPS78417QDBVRQ1	SOT-23	DBV	5	3000	210.0	185.0	35.0



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Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TPS78417QDBVRQ1	SOT-23	DBV	5	3000	210.0	185.0	35.0
TPS78418BQWDRBRQ1	SON	DRB	8	3000	367.0	367.0	35.0
TPS78418QDBVRQ1	SOT-23	DBV	5	3000	210.0	185.0	35.0
TPS78418QDBVRQ1	SOT-23	DBV	5	3000	210.0	185.0	35.0
TPS78418QWDRBRQ1	SON	DRB	8	3000	367.0	367.0	35.0
TPS78425BQWDRBRQ1	SON	DRB	8	3000	367.0	367.0	35.0
TPS78425QDBVRQ1	SOT-23	DBV	5	3000	210.0	185.0	35.0
TPS78425QDBVRQ1	SOT-23	DBV	5	3000	210.0	185.0	35.0
TPS78425QWDRBRQ1	SON	DRB	8	3000	367.0	367.0	35.0
TPS78428QDBVRQ1	SOT-23	DBV	5	3000	210.0	185.0	35.0
TPS78429QDBVRQ1	SOT-23	DBV	5	3000	210.0	185.0	35.0
TPS78430QDBVRQ1	SOT-23	DBV	5	3000	210.0	185.0	35.0
TPS78430QWDRBRQ1	SON	DRB	8	3000	367.0	367.0	35.0
TPS78433BQWDRBRQ1	SON	DRB	8	3000	367.0	367.0	35.0
TPS78433QDBVRQ1	SOT-23	DBV	5	3000	210.0	185.0	35.0
TPS78433QDBVRQ1	SOT-23	DBV	5	3000	210.0	185.0	35.0
TPS78433QWDRBRQ1	SON	DRB	8	3000	367.0	367.0	35.0
TPS78450QDBVRQ1	SOT-23	DBV	5	3000	210.0	185.0	35.0
TPS78450QWDRBRQ1	SON	DRB	8	3000	367.0	367.0	35.0



SMALL OUTLINE TRANSISTOR



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
 2. This drawing is subject to change without notice.
 3. Reference JEDEC MO-178.

- 4. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25 mm per side.
- 5. Support pin may differ or may not be present.



SMALL OUTLINE TRANSISTOR



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE TRANSISTOR



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



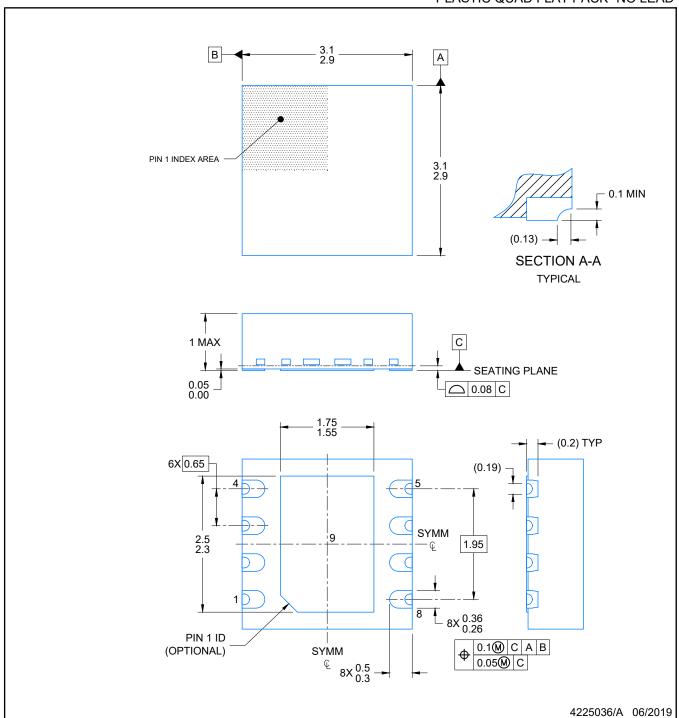


Images above are just a representation of the package family, actual package may vary. Refer to the product data sheet for package details.

4203482/L



PLASTIC QUAD FLAT PACK- NO LEAD

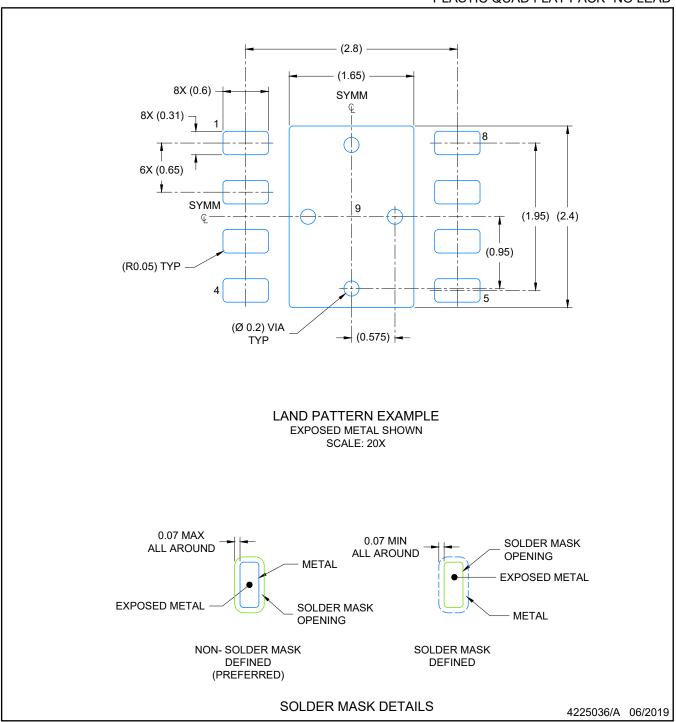


NOTES:

- All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. The package thermal pad must be soldered to the printed circuit board for optimal thermal and mechanical performance.



PLASTIC QUAD FLAT PACK- NO LEAD

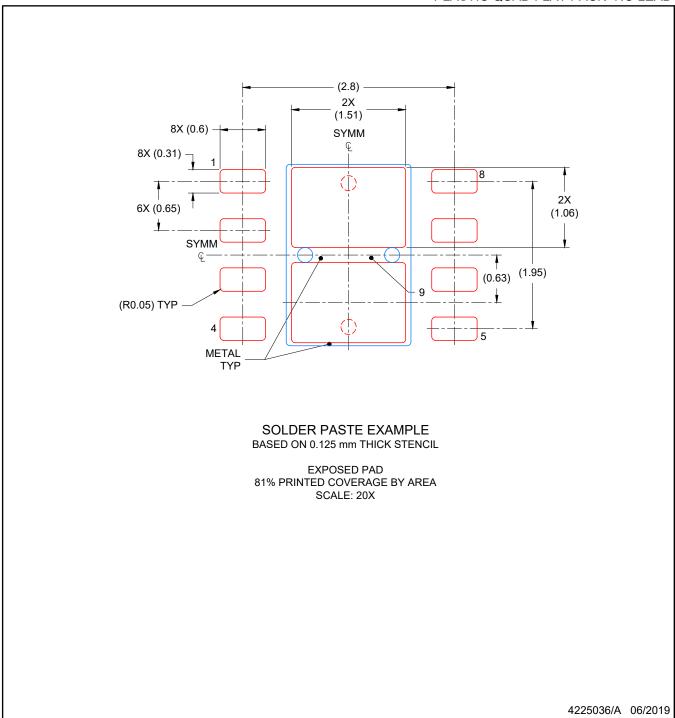


NOTES: (continued)

- 4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).
- 5. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.



PLASTIC QUAD FLAT PACK- NO LEAD



NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



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Last updated 10/2025